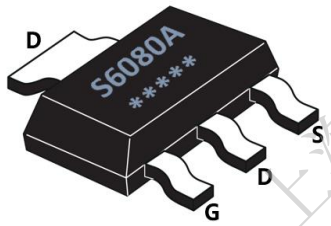
General Description:

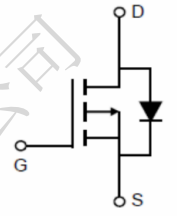
The LWS6080A23 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is SOT-223, which accords with the ROHS standard and Halogen Free standard.

V_{DSS}	-60	V
I_D	-5.0	A
P_D	3.0	W
$R_{DS(ON)\ TYPE}$	60	mΩ

Marking and Pin Assignment



Inner Equivalent Principium Chart



Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- Battery switching application
- Hard switched and high frequency circuits
- Power Management

Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S6080A/D.C.	LWS6080A23	SOT-223	Reel	3000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		-60	V
I_D	Continuous Drain Current	T_C=25℃	-5.0	A
	Continuous Drain Current	T_C=100℃	-3.1	A
I_{DM}[a1]	Pulsed Drain Current		-20	A
V_{GS}	Gate-to-Source Voltage		±20	V
P_D	Power Dissipation		3.0	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	℃
T_L	Maximum Temperature for Soldering		260	℃

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	41.6	℃/W

Electrical Characteristic (T_A = 25 °C, unless otherwise specified)**:**

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-60	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=-60V, V_{GS}=0V	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=-20V, V_{DS}=0V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=+20V, V_{DS}=0V	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1.3	-1.65	-2.1	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	V_{GS}=-10V, I_D=-5.0A	--	60	75	mΩ
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	V_{GS}=-4.5V, I_D=-4.0A	--	75	100	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} =-30V f = 1.0MHz	--	504	--	pF
C_{oss}	Output Capacitance		--	82	--	
C_{rss}	Reverse Transfer Capacitance		--	3.9	--	
R_G	Gate resistance	V_{GS}=0V,V_{DS} Open	--	3.0	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =-5A V_{DS} =-30V V_{GS} =-10V R_G = 3Ω	--	10	--	ns
t_r	Rise Time		--	6.0	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	40	--	
t_f	Fall Time		--	13	--	
Q_g	Total Gate Charge	V_{GS} =-10V V_{DS} = -30V I_D =-5A	--	10.5	--	nC
Q_{gs}	Gate Source Charge		--	2.8	--	
Q_{gd}	Gate Drain Charge		--	1.5	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_C =25 °C	--	--	-5.0	A
I_{SM}	Diode Pluse Current		--	--	-20	A
V_{SD}	Diode Forward Voltage	I_S=-5A, V_{GS}=0V	--	--	-1.2	V
t_{rr}	Reverse Recovery time	I_S=-5A, V_{DD}=-30V, dI/dt=100A/us	--	50	--	ns
Q_{rr}	Reverse Recovery Charge		--	105	--	nC

a1：Repetitive rating; pulse width limited by maximum junction temperature

Characteristics Curve：

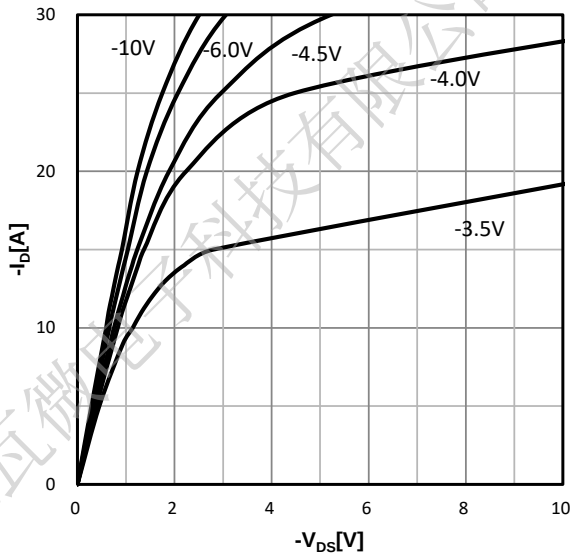
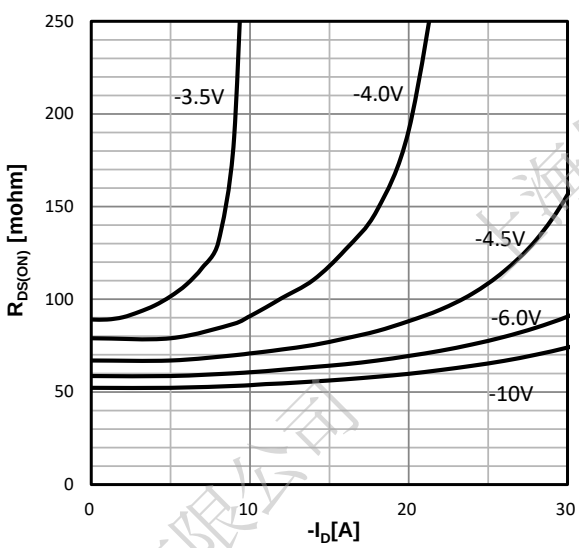
Figure 1: Typ. output characteristics	Figure 2: Typ. drain-source on resistance
	
$I_D=f(V_{DS})$, T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}=f(I_D)$, T_j=25 °C; parameter: V_{GS}

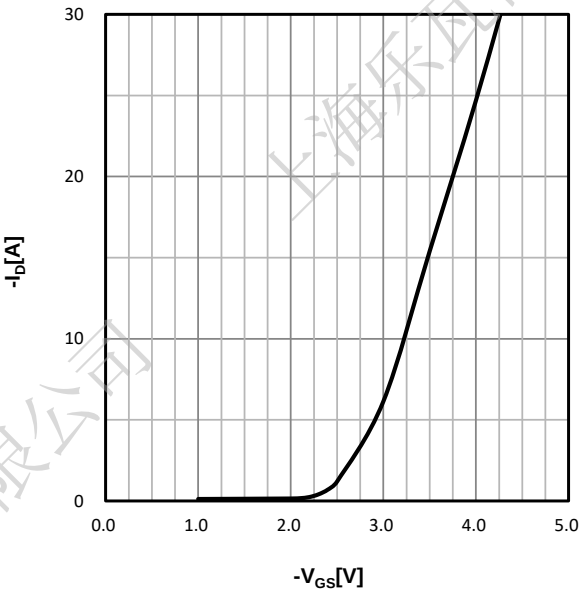
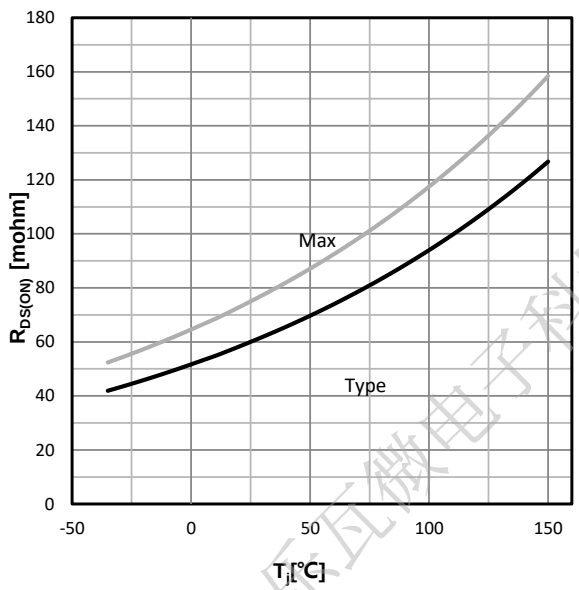
Figure 3: Typ. transfer characteristics	Figure 4: drain-source on resistance
	
$I_D=f(V_{GS})$, $\|V_{DS}\|>2\|I_D\|R_{DS}(on)max$;	$R_{DS(on)}=f(T_j)$, I_D=-5A, V_{GS}=-10V;

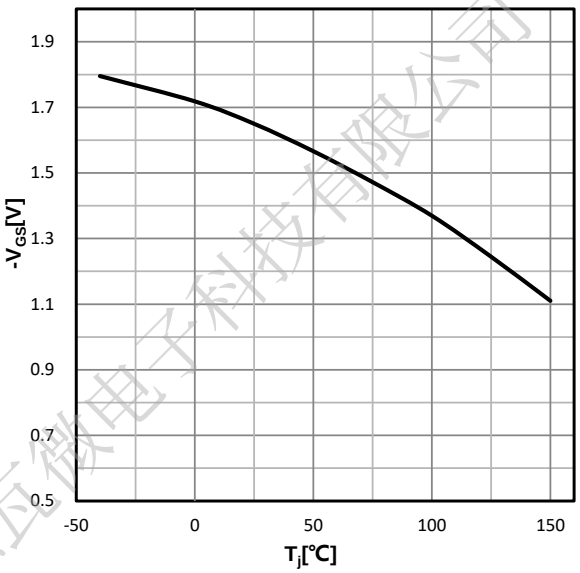
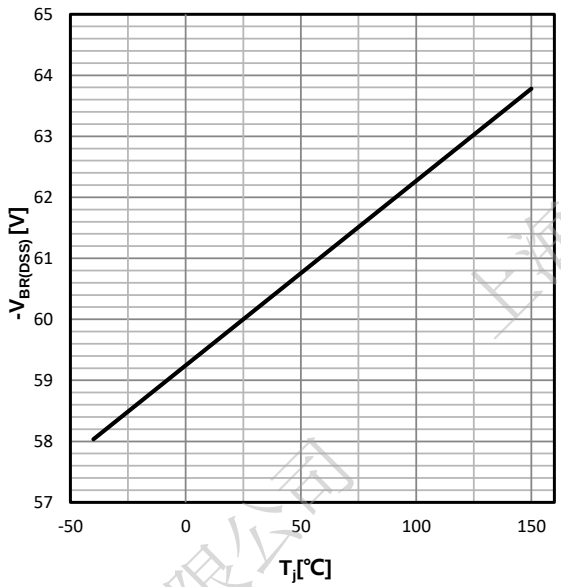
Figure 5: Typ. gate threshold voltage	Figure 6: Drain-source breakdown voltage
	
V_{GS}=f(T_j), V_{GS}=$V_{DS,}$ I_D=-250μA;	$V_{BR(DSS)}$=f(T_j); I_D=-250μA;

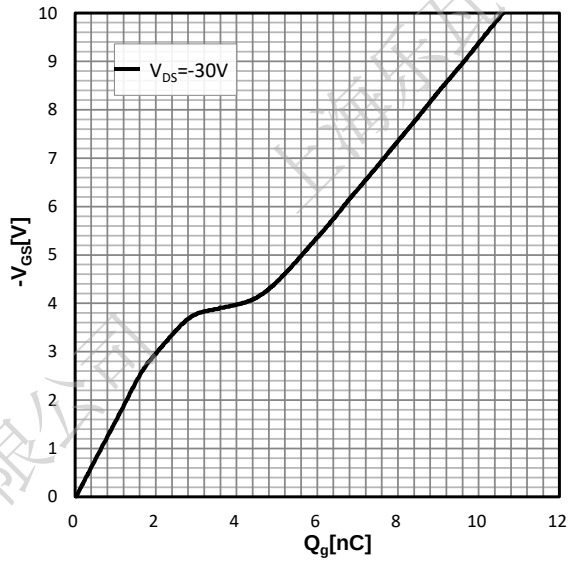
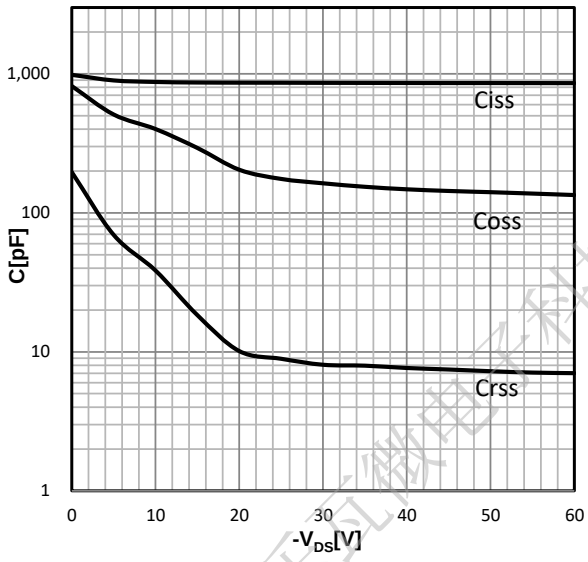
Figure 7: Typ. gate charge	Figure 8: Typ. Capacitances
	
V_{GS}=f(Q_g), I_D=-5A, T_j=25 °C; parameter: V_{DS}	C=f(V_{DS}); V_{GS}=0V; f=1.0 MHz;

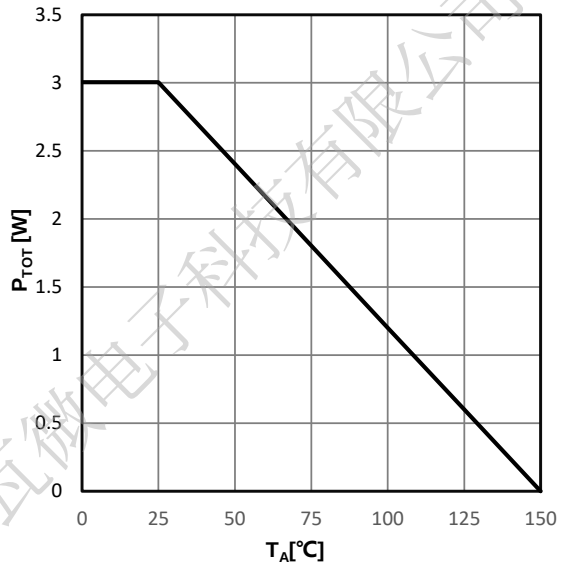
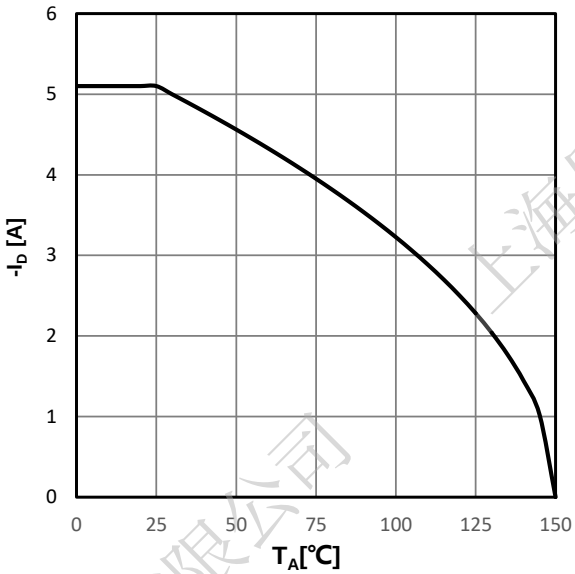
Figure 9: Power dissipation	Figure 10:Drain current
	
$P_{tot}=f(T_A)$;	$I_D=f(T_A)$;

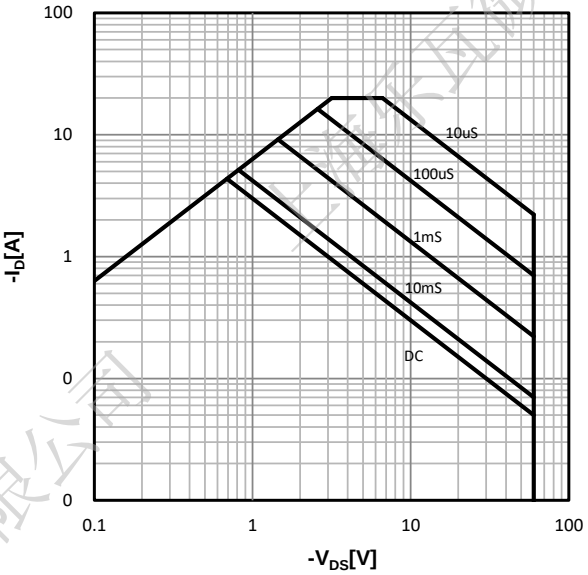
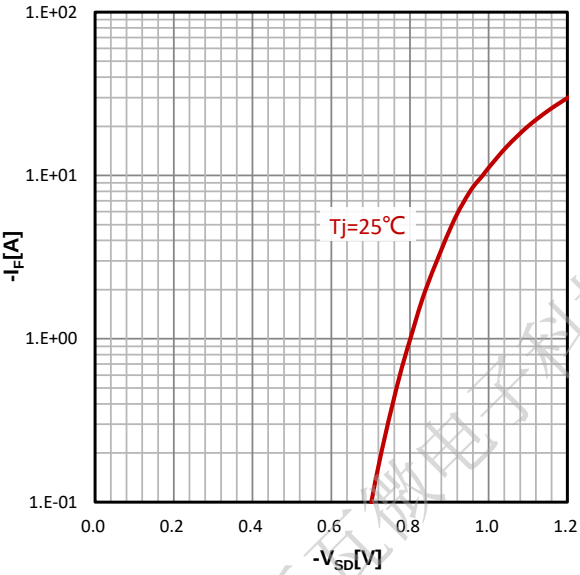
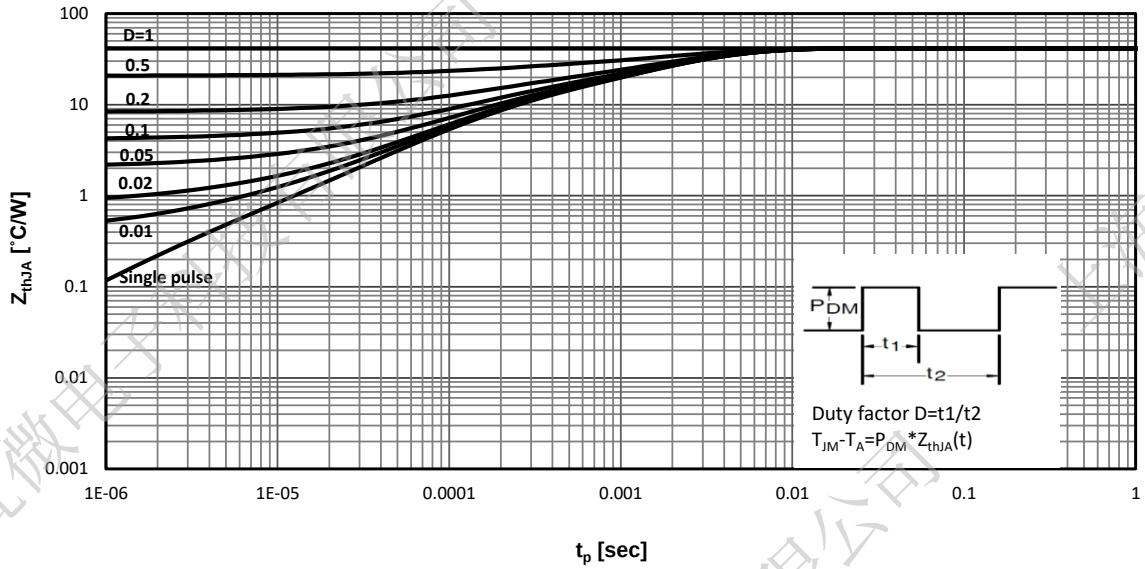
Figure 11: Safe operating area	Figure 12: Typ. forward characteristics
	
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: tp	$I_F=f(V_{SD})$;

Figure 13: Max. Transient Thermal Impedance



$Z_{thJA}=f(t_p)$; parameter: D

Test Circuit & Waveform:

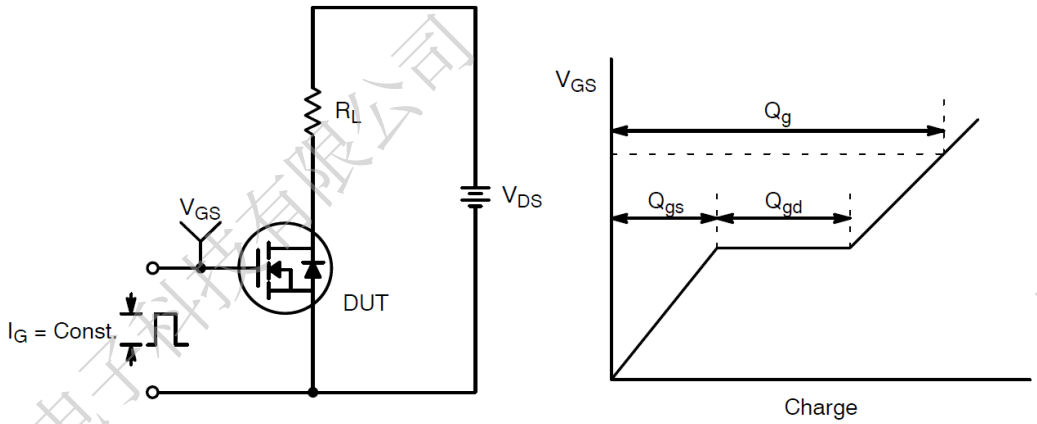


Figure 14: Gate Charge Test Circuit & Waveform

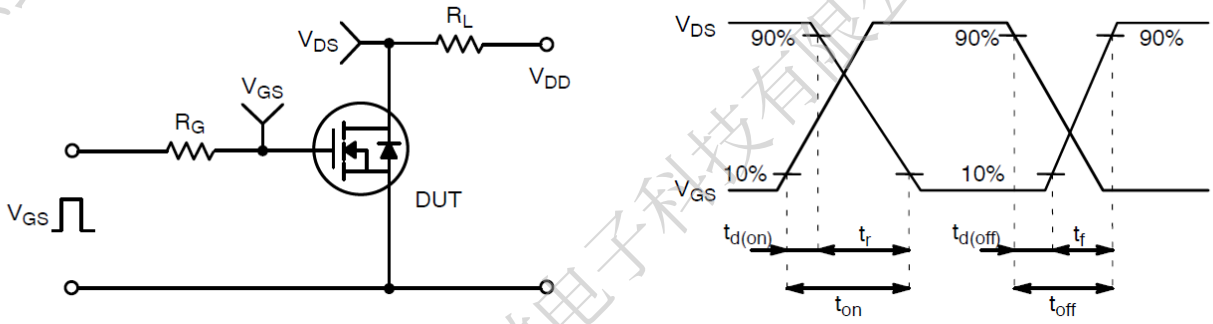


Figure 15: Resistive Switching Test Circuit & Waveforms

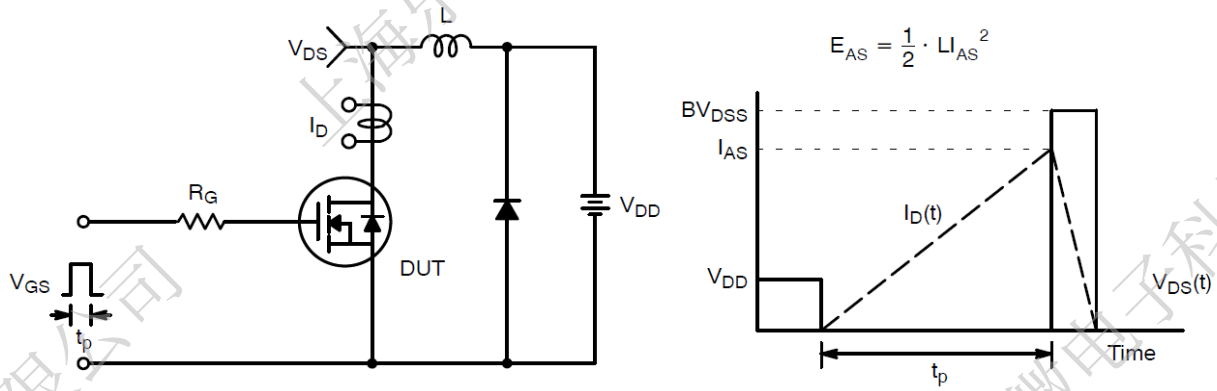
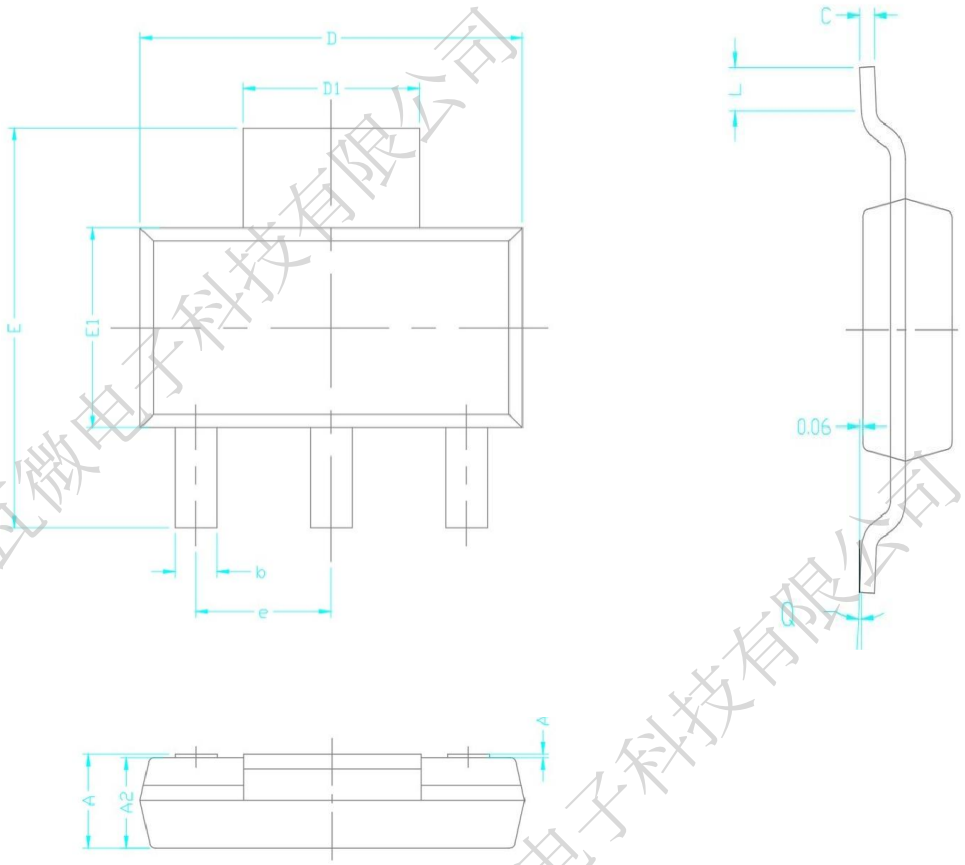


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:



COMMON DIMENSION (MM)			
PKG	**TO-223**		
Symbol	**MIN**	**NOM**	**MAX**
A	1.520	1.580	1.720
A1	0.010	0.060	0.150
A2	1.470	1.520	1.570
b	0.660	0.710	0.800
C	0.250	0.280	0.350
D	6.500	6.600	6.750
D1	2.900	3.000	3.100
E	6.700	7.000	7.300
E1	3.300	3.500	3.700
L	0.750 REF		
e	2.300 REF		
Q	0°	4°	10°

Revision History:

Revison	Date	Descriptions
Rev 1.0	Dec.2021	Initial Version

Disclaimer:

The information in this document is believed to be accurate and reliable. However, no responsibility is assumed by LW-Micro for its use. All operating parameters must be designed, validated and tested to ensure they meet the requirements of your application. LW-Micro reserves the right to make any specification and/or circuitry changes without prior notification. Before starting a brand-new project, please contact LW-Micro Sales to get the most recent relevant information.

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